

PATENT

AMENDMENTS TO THE SPECIFICATION

Please amend the title in all instances as follows:

BIPOLAR TRANSISTOR WITH AN ULTRA SMALL SELF-ALIGNED POLYSILICON  
~~EMITTER AND METHOD OF FORMING THE SILICON GERMANIUM BASE OF THE~~  
TRANSISTOR

Please amend the first paragraph on page 1 as follows:

*Ex.*  
~~The present application~~ This is a divisional application of Application Serial No.  
09/994,293 filed on November 26, 2002, <sup>Pat. 6,253,234</sup> ~~which is a~~ continuation-in-part of  
<sup>Pat. 6,049,482</sup>  
Application Serial No. 09/882,740 filed June 15, 2001, by Abdalla Aly Naem for  
Bipolar Transistor with a Silicon Germanium Base and an Ultra Small Self-Aligned  
Polysilicon Emitter and Method of Forming the Transistor.